Drafts
Pending
Active
 L1: (43959) nitride.clm. or (silicon adj nit
 L2: (678) 1 and ((anti adj reflective) or an
 L3: (367) 2 and (nitride near layer)
 L4: (239) 3 and (silicon near nitride).clm.
 L5: (37) 4 and ((antireflective or (anti adj
 L6: (18) 5 and (silicon adj rich)
Failed
 (0) 2 near nitride
Saved
 (8) (("6475874") or ("6372561") or ("6365445
 (5) (("6524954") or ("6475874") or ("6316362
 (2) (("6107176") or ("6177335")).PN.
 (1) ("5633177").PN.
 (17) ("4558507" | "4636822" | "4683645" | "4
 (2472) boron.clm. and gate.clm.
 (0) (boron.clm. and gate.clm.) and (large ne
 (52) (boron.clm. and gate.clm.) and (implant
 (1) ("5633177").PN.
Favorites

USPAT; USOCR

5 and (silicon adj rich)

U	I	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C	Image
5				US 6287951 B1	20010911	17	Process for forming a combination hardmask an	438/618	438/636; 438/637;		Lucas, Kevin D. et al.			US 628
6		✓		US 6174844 B1	20010116	6	Anti-reflective silicon nitride film using in-s	430/272.1	257/437; 257/E21.02		Shieh, Meng-Shiun et al.	✓		US 617
7		✓		US 6174590 B1	20010116	19	Isolation using an antireflective coating	428/209	257/E21.55 2;		Iyer, Ravi et al.	✓		US 617
8				US 6121133 A	20000919	17	Isolation using an antireflective coating	438/636	257/E21.02 9;		Iyer, Ravi et al.	✓		US 612
9				US 5948598	19990907	7	Anti-reflective silicon nitride film using in-s	430/311	257/E21.02 9;		Shieh, Meng-Shiun et al.	✓		US 594
10				US 5918147	19990629	14	Process for forming a semiconductor device wi	438/636	257/E21.02 9;		Filipiak, Stanley M. et al.	✓		US 591
11				US 5872385 A	19990216	8	Conductive interconnect structure and method of	257/437	257/413; 257/649;		Taft, Robert C. et al.	✓		US 587
12		✓		US 5639687	19970617	8	Method for forming an integrated circuit part	438/69	257/E21.02 9;		Roman, Bernard John et al.	✓		US 563
13				US 5539249	19960723	7	Method and structure for forming an integrat	257/649	257/437; 257/640;		Roman, Bernard J.	✓		US 553
14		✓		US 5441914 A	19950815	8	Method of forming conductive interconnect	438/592	148/DIG.1; 148/DIG.12		Taft, Robert C. et al.	✓		US 544
15				US 5378659 A	19950103	7	Method and structure for forming an integrat	438/761	257/E21.02 9;		Roman, Bernard J. et al.	✓		US 537